

Complementary MOSFET

ELM4C2901FEA-S

<http://www.elm-tech.com>

■General description

ELM4C2901FEA-S uses advanced trench technology to provide excellent $R_{ds(on)}$, low gate charge and low gate threshold voltage.

■Features

N-channel

- $V_{ds}=20V$
- $I_d=3.8A(V_{gs}=4.5V)$
- $R_{ds(on)} = 50m\Omega(V_{gs}=4.5V)$
- $R_{ds(on)} = 75m\Omega(V_{gs}=2.5V)$
- $R_{ds(on)} = 100m\Omega(V_{gs}=1.8V)$

P-channel

- $V_{ds}=-20V$
- $I_d=-2.5A(V_{gs}=-4.5V)$
- $R_{ds(on)} = 70m\Omega(V_{gs}=-4.5V)$
- $R_{ds(on)} = 95m\Omega(V_{gs}=-2.5V)$
- $R_{ds(on)} = 115m\Omega(V_{gs}=-1.8V)$

■Maximum absolute ratings

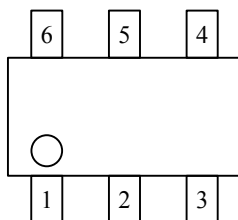
Parameter		Symbol	N-ch (Max.)	P-ch (Max.)	Unit	Note
Drain-source voltage		V_{ds}	20	-20	V	
Gate-source voltage		V_{gs}	± 12	± 12	V	
Continuous drain current ($V_{gs}=4.5V$)	$T_a=25^{\circ}C$	I_d	3.8	-2.5	A	1
	$T_a=70^{\circ}C$		3.0	-2.0		
Pulsed drain current		I_{dm}	15	-15	A	2
Power dissipation	$T_c=25^{\circ}C$	P_d	1.1	1.1	W	3
Storage temperature range		T_{stg}	-55 to 150	-55 to 150	$^{\circ}C$	
Operating junction temperature range		T_j	-55 to 150	-55 to 150	$^{\circ}C$	

■Thermal Characteristics

Parameter	Symbol	Typ.	Max.	Unit	Note
Thermal resistance junction-to-ambient	$R_{\theta ja}$	-	110	$^{\circ}C/W$	1
Thermal resistance junction-case	$R_{\theta jc}$	-	70	$^{\circ}C/W$	1

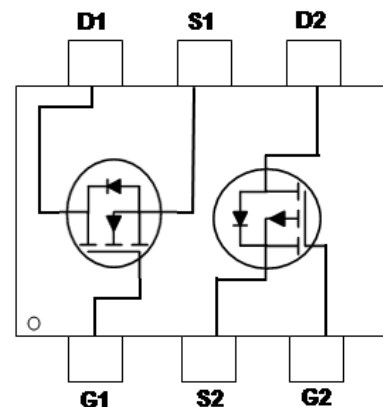
■Pin configuration

SOT-26(TOP VIEW)



Pin No.	Pin name
1	GATE1
2	SOURCE2
3	GATE2
4	DRAIN2
5	SOURCE1
6	DRAIN1

■Circuit



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■Electrical characteristics (N-ch)

T_j=25°C. Unless otherwise noted.

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	Note
STATIC PARAMETERS							
Drain-source breakdown voltage	BV _{dss}	V _{gs} =0V, I _d =250μA	20	-	-	V	
Static drain-source on-resistance	R _{ds(on)}	V _{gs} =4.5V, I _d =4A	-	-	50	mΩ	2
		V _{gs} =2.5V, I _d =3A	-	-	75		
		V _{gs} =1.8V, I _d =2A	-	-	100		
Gate threshold voltage	V _{gs(th)}	V _{gs} =V _{ds} , I _d =250μA	0.35	-	1.00	V	
Drain-source leakage current	I _{dss}	V _{ds} =16V, V _{gs} =0V	-	-	1	μA	
		V _{ds} =16V, V _{gs} =0V, T _j =55°C	-	-	5		
Gate-source leakage current	I _{gss}	V _{gs} =±12V, V _{ds} =0V	-	-	±100	nA	
Forward transconductance	G _{fs}	V _{ds} =5V, I _d =4A	-	30	-	S	
Continuous source current	I _s	V _{gs} =V _{ds} =0V, Force current	-	-	1.5	A	1, 4
Diode forward voltage	V _{sd}	V _{gs} =0V, I _s =1A	-	-	1.2	V	2
DYNAMIC PARAMETERS							
Input capacitance	C _{iss}	V _{ds} =15V, V _{gs} =0V, f=1MHz	-	670	-	pF	
Output capacitance	C _{oss}		-	75	-	pF	
Reverse transfer capacitance	C _{rss}		-	68	-	pF	
SWITCHING PARAMETERS							
Total gate charge (4.5V)	Q _g	V _{ds} =15V, V _{gs} =4.5V I _d =4A	-	8.60	-	nC	
Gate-source charge	Q _{gs}		-	1.37	-	nC	
Gate-drain charge	Q _{gd}		-	2.30	-	nC	
Turn-on delay time	t _{d(on)}	V _{ds} =10V, V _{gs} =4.5V R _{gen} =3.3Ω, I _d =4A	-	5.2	-	ns	
Turn-on rise time	t _r		-	34.0	-	ns	
Turn-off delay time	t _{d(off)}		-	23.0	-	ns	
Turn-off fall time	t _f		-	9.2	-	ns	
Reverse recovery time	t _{rr}	I _f =4A, di/dt=100A/μs	-	8.9	-	nS	
Reverse recovery charge	Q _{rr}		-	1.7	-	nC	

NOTE :

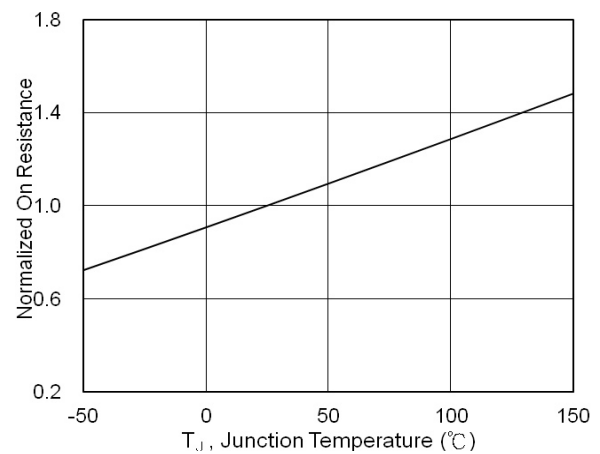
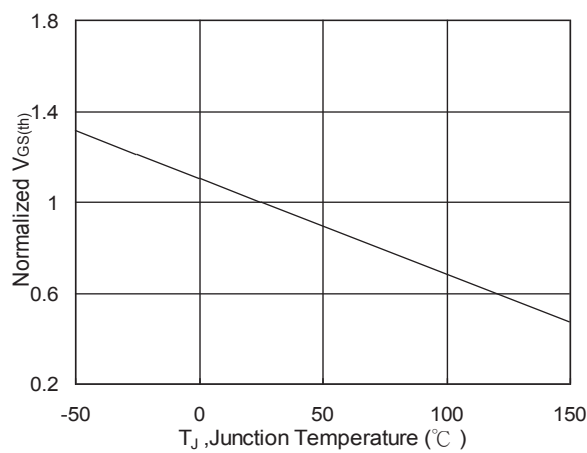
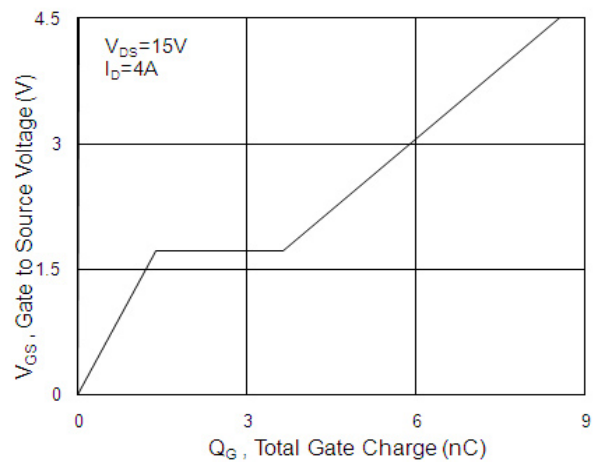
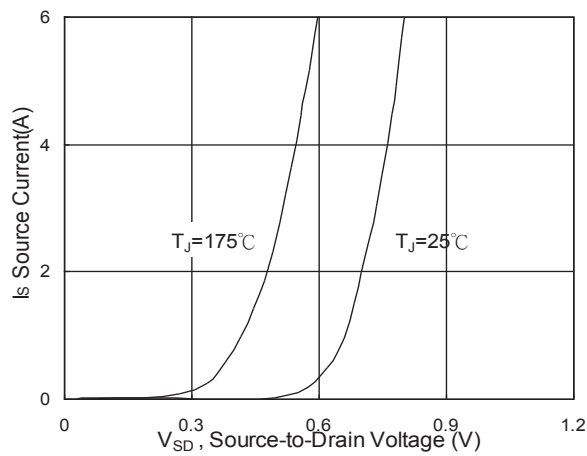
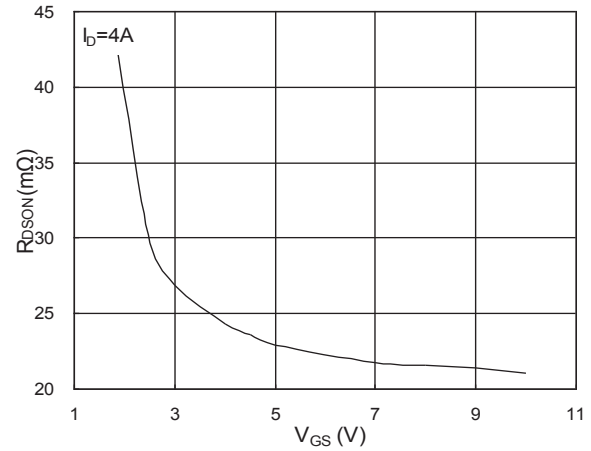
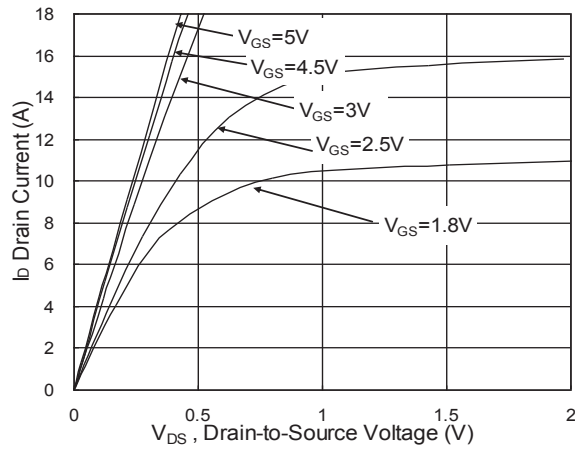
1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width ≤ 300μs and duty cycle ≤ 2%.
3. The power dissipation is limited by 150°C junction temperature.
4. The data is theoretically the same as I_d and I_{dm}, in real applications, should be limited by total power dissipation.

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■ Typical electrical and thermal characteristics (N-ch)



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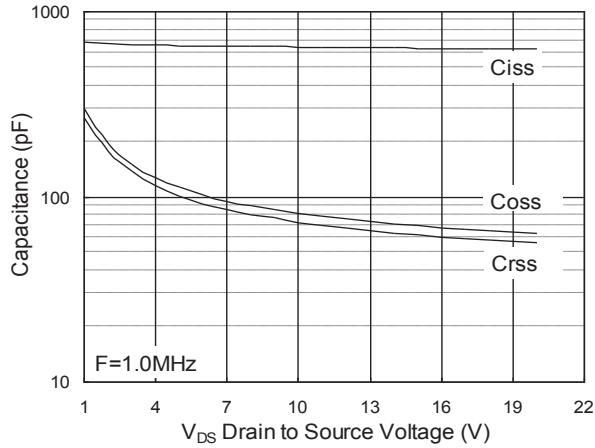


Fig.7 Capacitance

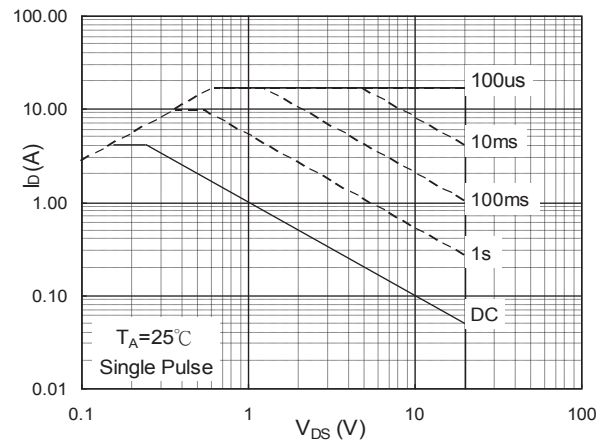


Fig.8 Safe Operating Area

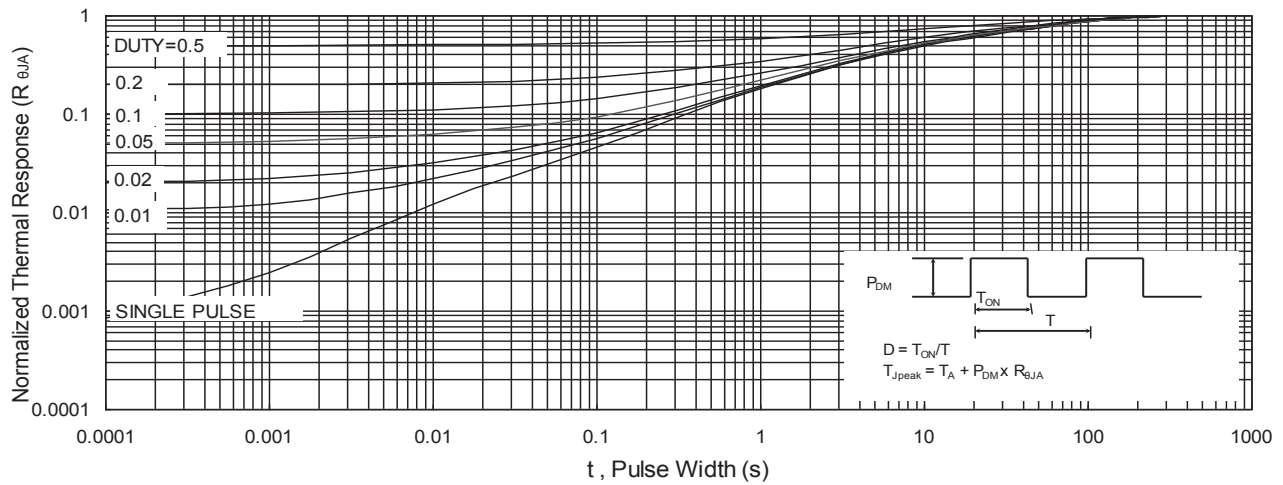


Fig.9 Normalized Maximum Transient Thermal Impedance

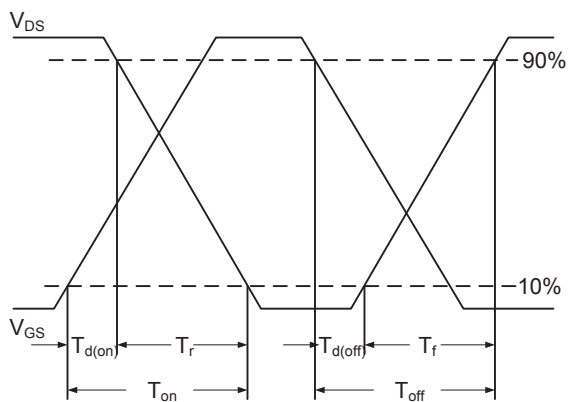


Fig.10 Switching Time Waveform

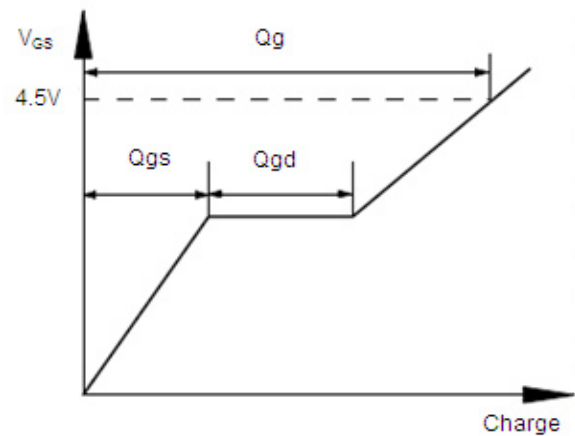


Fig.11 Gate Charge Waveform

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■Electrical Characteristics (P-ch)

T_j=25°C. Unless otherwise noted.

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	Note
STATIC PARAMETERS							
Drain-source breakdown voltage	BV _{dss}	V _{gs} =0V, I _d =-250μA	-20	-	-	V	
Static drain-source on-resistance	R _{ds(on)}	V _{gs} =-4.5V, I _d =-2.5A	-	-	70	mΩ	2
		V _{gs} =-2.5V, I _d =-2.0A	-	-	95		
		V _{gs} =-1.8V, I _d =-1.0A	-	-	115		
Gate threshold voltage	V _{gs(th)}	V _{gs} =V _{ds} , I _d =-250μA	-0.4	-	-1.0	V	
Drain-source leakage current	I _{dss}	V _{ds} =-16V, V _{gs} =0V	-	-	-1	μA	
		V _{ds} =-16V, V _{gs} =0V, T _j =55°C	-	-	-5		
Gate-source leakage current	I _{gss}	V _{gs} =±12V, V _{ds} =0V	-	-	±100	nA	
Forward transconductance	G _{fs}	V _{ds} =-5V, I _d =-3A	-	9	-	S	
Continuous source current	I _s	V _{gs} =V _{ds} =0V, Force current	-	-	-1.5	A	1, 4
Diode forward voltage	V _{sd}	V _{gs} =0V, I _s =-1A	-	-	-1.2	V	2
DYNAMIC PARAMETERS							
Input capacitance	C _{iss}	V _{ds} =-15V, V _{gs} =0V, f=1MHz	-	686.0	-	pF	
Output capacitance	C _{oss}		-	90.8	-	pF	
Reverse transfer capacitance	C _{rss}		-	80.4	-	pF	
SWITCHING PARAMETERS							
Total gate charge (-4.5V)	Q _g	V _{ds} =-15V, V _{gs} =-4.5V I _d =-3A	-	9.70	-	nC	
Gate-source charge	Q _{gs}		-	2.05	-	nC	
Gate-drain charge	Q _{gd}		-	2.43	-	nC	
Turn-on delay time	t _{d(on)}	V _{ds} =-10V, V _{gs} =-4.5V R _{gen} =3.3Ω, I _d =-3A	-	4.8	-	ns	
Turn-on rise time	t _r		-	9.6	-	ns	
Turn-off delay time	t _{d(off)}		-	52.0	-	ns	
Turn-off fall time	t _f		-	8.4	-	ns	
Reverse recovery time	t _{rr}	I _f =-3A, di/dt=100A/μs	-	10.2	-	nS	
Reverse recovery charge	Q _{rr}		-	2.5	-	nC	

NOTE :

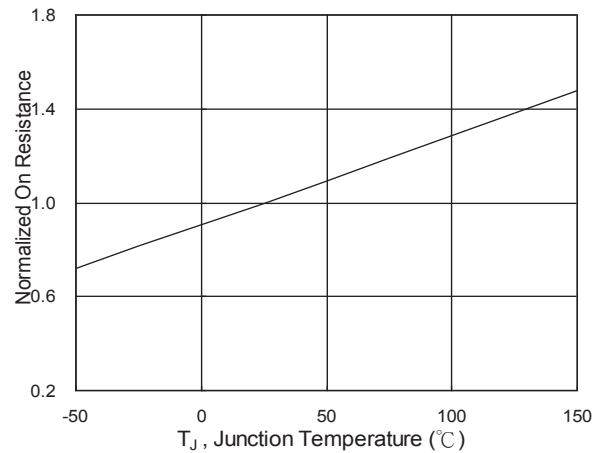
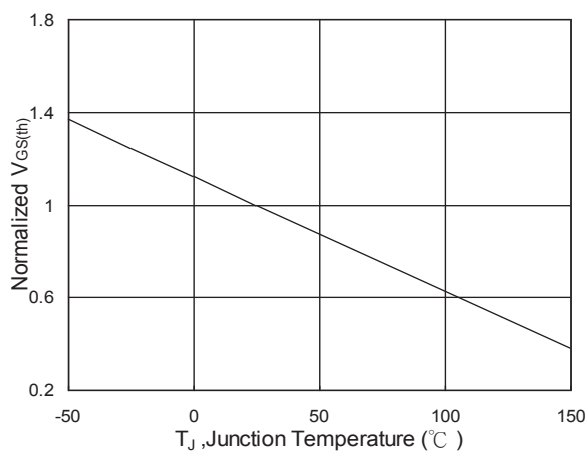
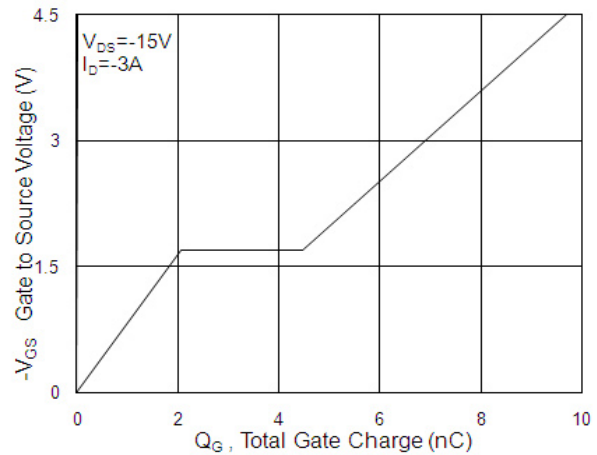
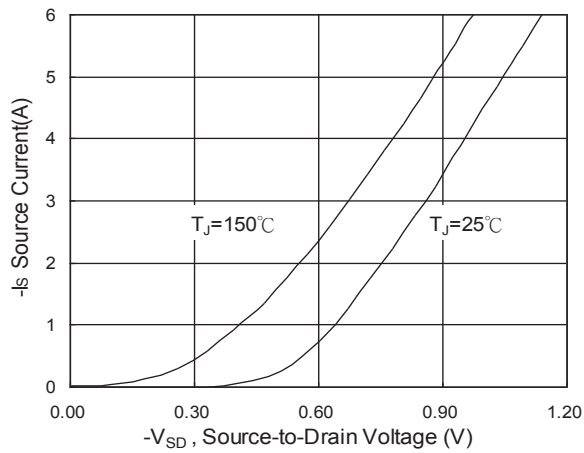
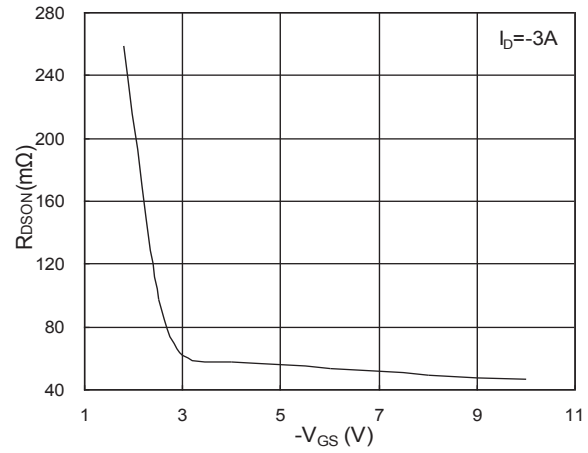
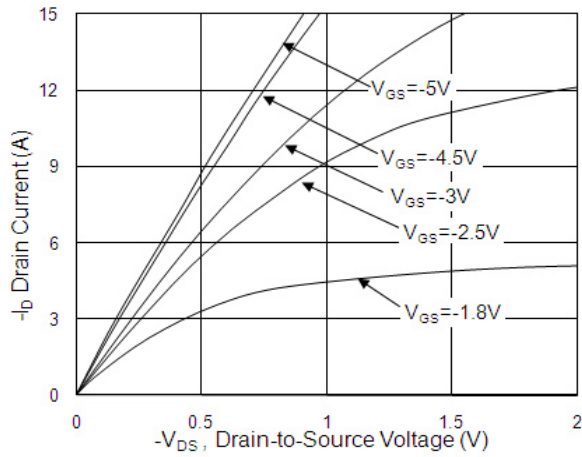
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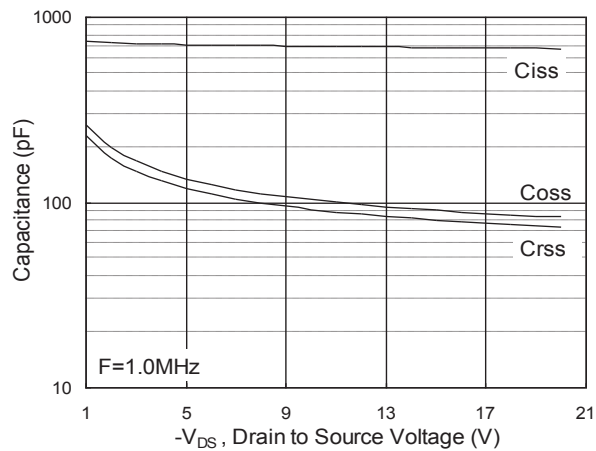


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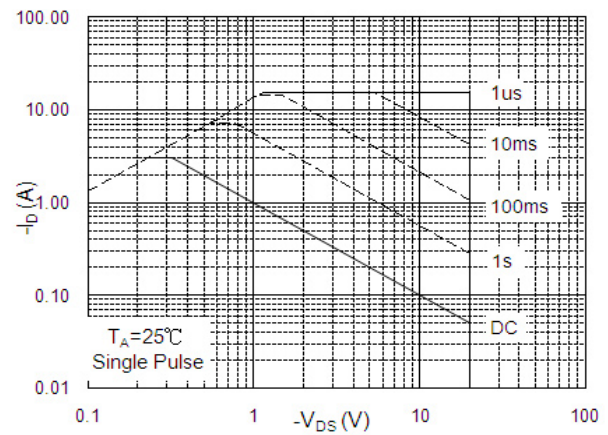


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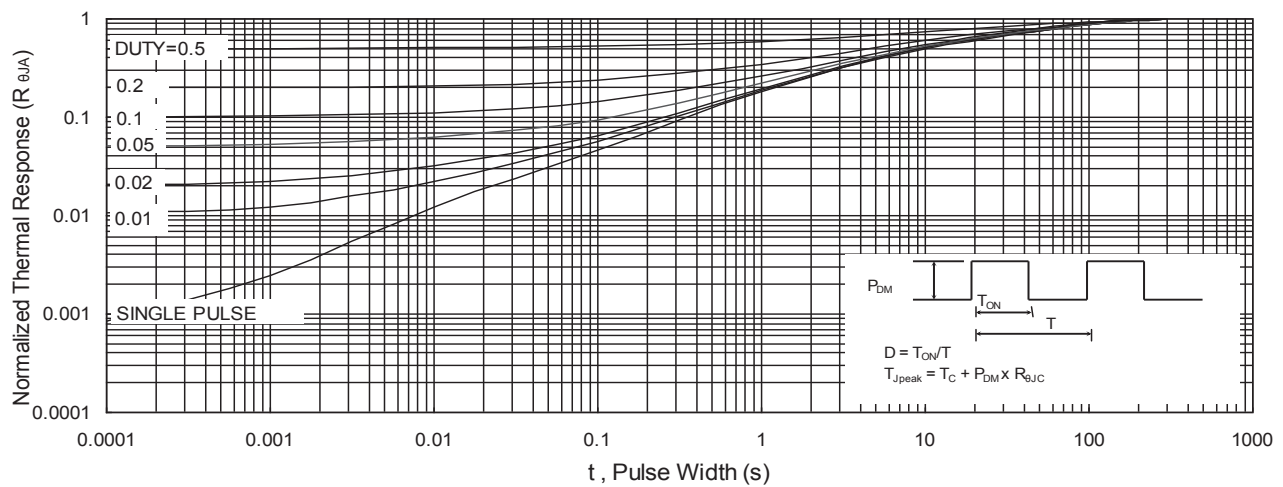


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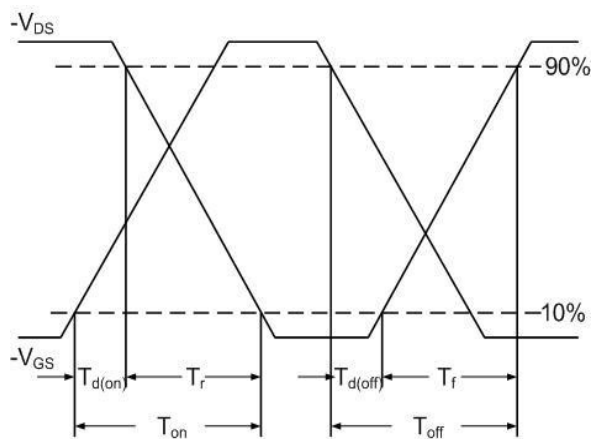


Fig.10 Switching Time Waveform

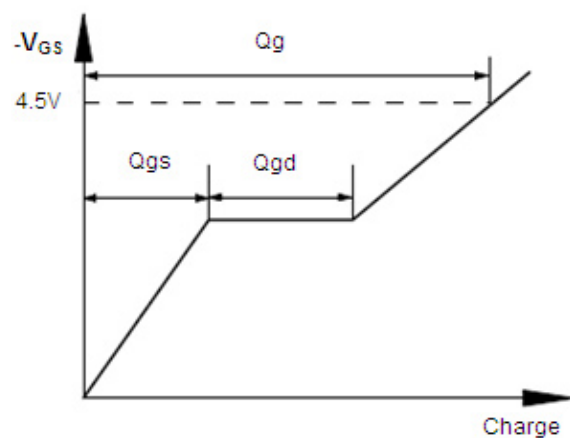


Fig.11 Gate Charge Waveform